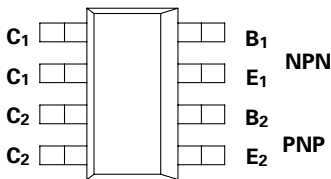


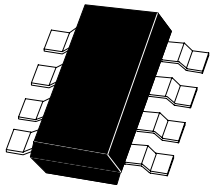
SM-8 COMPLEMENTARY MEDIUM POWER HIGH GAIN TRANSISTORS

ISSUE 1 - NOVEMBER 1995

ZDT6790



PARTMARKING DETAIL – T6790



**SM-8
(8 LEAD SOT223)**

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	NPN	PNP	UNIT
Collector-Base Voltage	V_{CBO}	45	-50	V
Collector-Emitter Voltage	V_{CEO}	45	-40	V
Emitter-Base Voltage	V_{EBO}	5	-5	V
Peak Pulse Current	I_{CM}	6	-6	A
Continuous Collector Current	I_C	2	-2	A
Operating and Storage Temperature Range	$T_J:T_{stg}$	-55 to +150		°C

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	VALUE	UNIT
Total Power Dissipation at $T_{amb} = 25^{\circ}C^*$ Any single die "on" Both die "on" equally	P_{tot}	2.25 2.75	W W
Derate above $25^{\circ}C^*$ Any single die "on" Both die "on" equally		18 22	mW/ °C mW/ °C
Thermal Resistance - Junction to Ambient* Any single die "on" Both die "on" equally		55.6 45.5	°C/ W °C/ W

* The power which can be dissipated assuming the device is mounted in a typical manner on a PCB with copper equal to 2 inches square.

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NPN TRANSISTOR ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	45			V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	45			V	$I_C = 10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E = 100\mu\text{A}$
Collector Cutoff Current	I_{CBO}			0.1	μA	$V_{CB} = 35\text{V}$
Emitter Cutoff Current	I_{EBO}			0.1	μA	$V_{EB} = 4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.1 0.5	V V	$I_C = 0.1\text{A}, I_B = 0.5\text{mA}^*$ $I_C = 1\text{A}, I_B = 5\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			0.9	V	$I_C = 1\text{A}, I_B = 10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			0.9	V	$I_C = 1\text{A}, V_{CE} = 2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	500 400 150				$I_C = 100\text{mA}, V_{CE} = 2\text{V}^*$ $I_C = 1\text{A}, V_{CE} = 2\text{V}^*$ $I_C = 2\text{A}, V_{CE} = 2\text{V}^*$
Transition Frequency	f_T	150			MHz	$I_C = 50\text{mA}, V_{CE} = 5\text{V}$ $f = 50\text{MHz}$
Input Capacitance	C_{ibo}		200		pF	$V_{EB} = 0.5\text{V}, f = 1\text{MHz}$
Output Capacitance	C_{obo}		16		pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$
Switching Times	t_{on} t_{off}		33 1300		ns	$I_C = 500\text{mA}, I_B = 50\text{mA}$ $I_{B2} = 50\text{mA}, V_{CC} = 10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
For typical characteristics graphs see FZT690 datasheet.

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PNP TRANSISTOR

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-50			V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40			V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu\text{A}$
Collector Cutoff Current	I_{CBO}			-0.1	μA	$V_{CB} = -30\text{V}$
Emitter Cutoff Current	I_{EBO}			-0.1	μA	$V_{EB} = -4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.25 -0.45 -0.75	V V V	$I_C = -500\text{mA}$, $I_B = -5\text{mA}^*$ $I_C = -1\text{A}$, $I_B = -10\text{mA}^*$ $I_C = -2\text{A}$, $I_B = -50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-1.0	V	$I_C = -1\text{A}$, $I_B = -10\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.75		V	$I_C = -1\text{A}$, $V_{CE} = -2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	300 250 200 150		800		$I_C = -10\text{mA}$, $V_{CE} = -2\text{V}$ $I_C = -500\text{mA}$, $V_{CE} = -2\text{V}^*$ $I_C = -1\text{A}$, $V_{CE} = -2\text{V}^*$ $I_C = -2\text{A}$, $V_{CE} = -2\text{V}^*$
Transition Frequency	f_T	100			MHz	$I_C = -50\text{mA}$, $V_{CE} = -5\text{V}$ $f = 50\text{MHz}$
Input Capacitance	C_{ibo}		225		pF	$V_{EB} = -0.5\text{V}$, $f = 1\text{MHz}$
Output Capacitance	C_{obo}		24		pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{on} t_{off}		35 600		ns	$I_C = -500\text{mA}$, $I_{B1} = -50\text{mA}$ $I_{B2} = -50\text{mA}$, $V_{CC} = -10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

For typical characteristics graphs see FZT790 datasheet.